

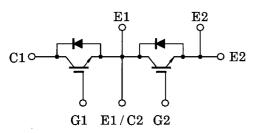
TOSHIBA GTR Module Silicon N Channel IGBT

MG150Q2YS50

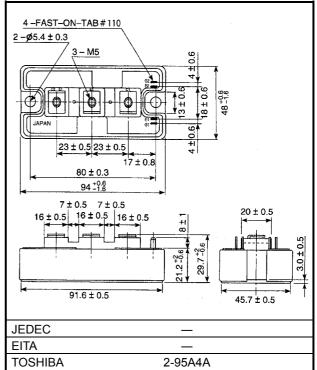
High Power Switching Applications Motor Control Applications

- High input impedance
- High speed : $t_f = 0.3 \mu s$ (Max) @Inductive load
- Low saturation voltage
- : V_{CE} (sat) = 3.6V (Max)
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

Equivalent Circuit



Maximum Ratings (Ta = 25°C)



Weight: 255g

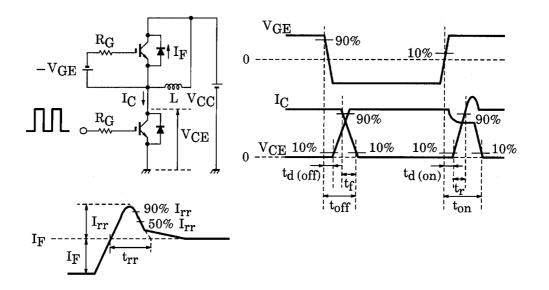
Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	I _C (25°C / 80°C)	200 / 150	A	
	1ms	I _{CP} (25°C / 80°C)	400 / 300		
Forward current	DC	١ _F	150	A	
	1ms	I _{FM}	300		
collector power dissipation (Tc = 25°C)		P _C	1250	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		—	3 / 3	N∙m	

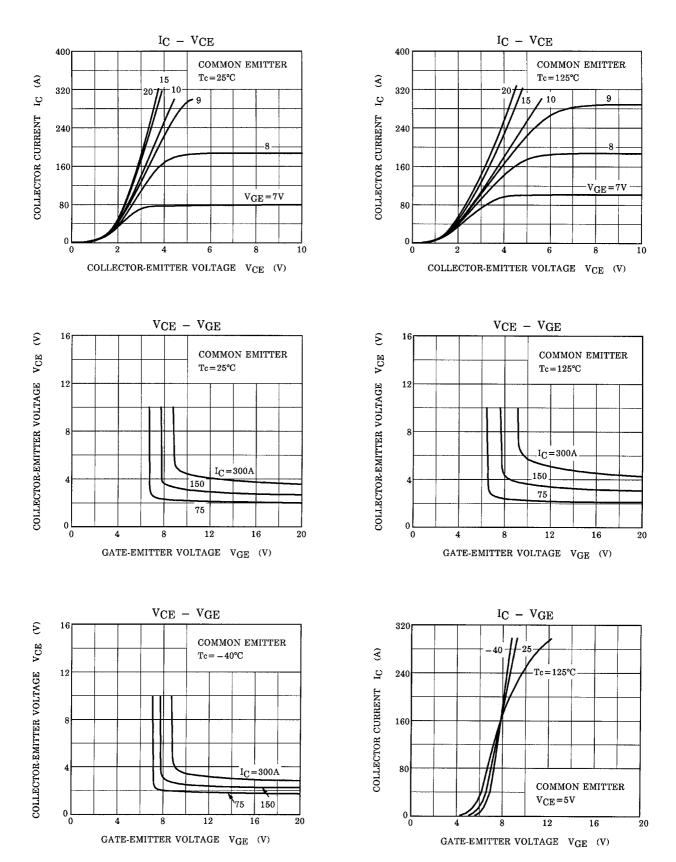
Unit: mm

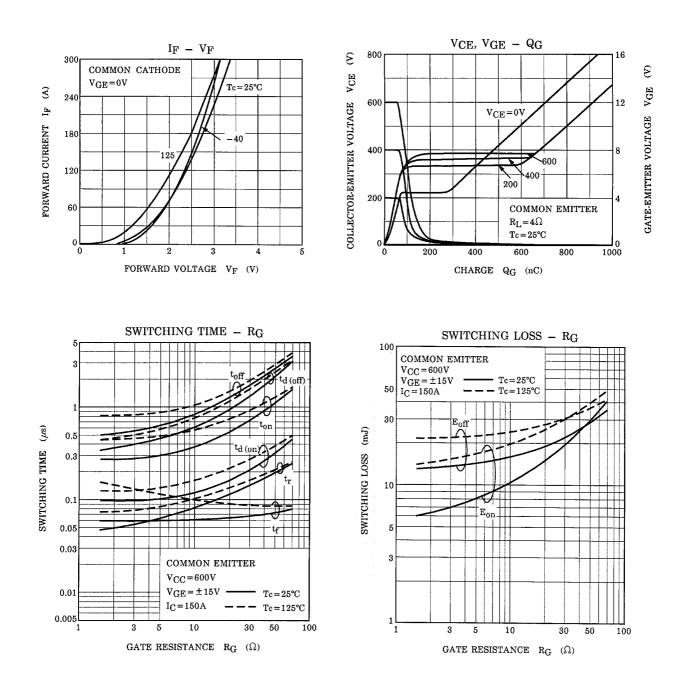
Electrical Characteristics (Ta = 25°C)

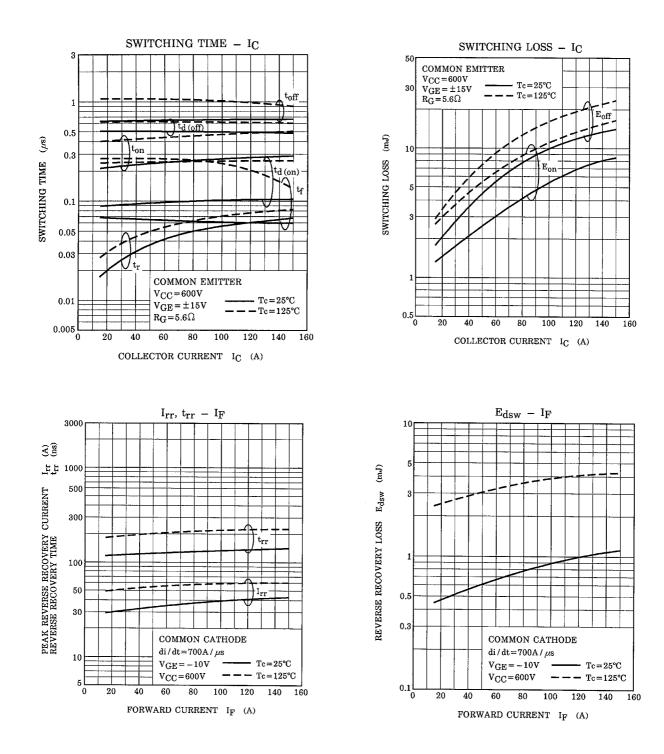
Char	Characteristic Symbol Test Condition		ondition	Min	Тур.	Max	Unit	
Gate leakage current		I _{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$		_	—	±500	nA
Collector cut-off current		ICES	V _{CE} = 1200V, V _{GE} = 0			_	2.0	mA
Gate-emitter cut-	ver cut-off voltage $V_{GE (off)}$ I _C = 150mA, V _{CE} = 5V		5V	3.0	_	6.0	V	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 150A, V _{GE} = 15V	T _j = 25°C	_	2.8	3.6	v
				T _j = 125°C	_	3.1	4.0	
Input capacitance	e	C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz		_	18.0	—	nF
Rise time Turn-on time	Turn-on delay time	t _{d(on)}		_	0.05	—		
	Rise time	t _r	Inductive load	_	0.05	_		
	Turn-on time	t _{on}	V _{CC} = 600V I _C = 150A		_	0.2	_	
	Turn-off delay time	t _{d(off)}	V _{GE} = ±15V R _G = 5.6Ω	_	0.5	_	μs	
	Fall time	t _f	(Note		_	0.1		0.3
	Turn-off time	t _{off}			_	0.6	_	
Forward voltage	•	VF	I _F = 150A, V _{GE} = 0		_	2.4	3.5	V
Reverse recovery time		t _{rr}	I _F = 150A, V _{GE} = -10V di / dt = 700A / μs (Note 1)		_	0.1	0.25	μs
Thermal resistance		R _{th (j-c)}	Transistor stage		_	—	0.1	°C/W
			Diode stage		_	—	0.32	

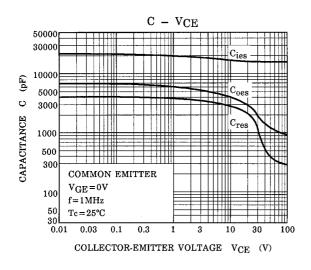
Note 1: Switching time and reverse recovery time test circuit & timing chart

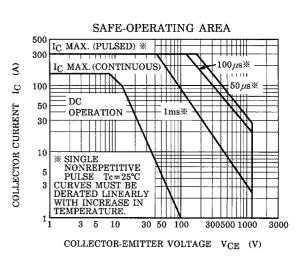


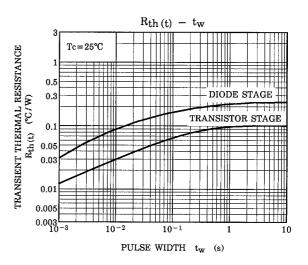


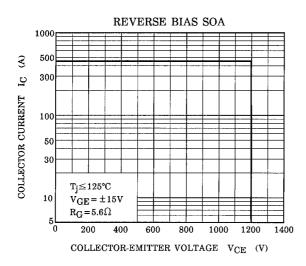


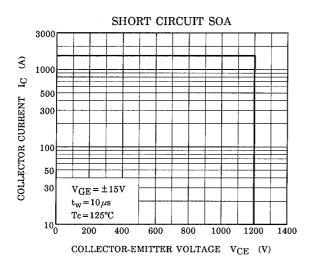












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